

Dual Common Cathode Schottky Rectifier, 15A (7.5A x 2)



FEATURES

- 150°C T_J operation
- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness, long term reliability and overvoltage protection
- Compliant to RoHS
- Designed and qualified according to JEDEC-JESD47
- Solder bath temperature 275°C maximum, 10 s per JESD 22B-106 (for TO-220AB and ITO-220AB package)

DESCRIPTION

The **MBR15xxCT** Schottky rectifier has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 150°C junction temperature.

APPLICATIONS

- Switching mode power supplies
- DC to DC converters
- Freewheeling diodes
- Reverse battery protection.

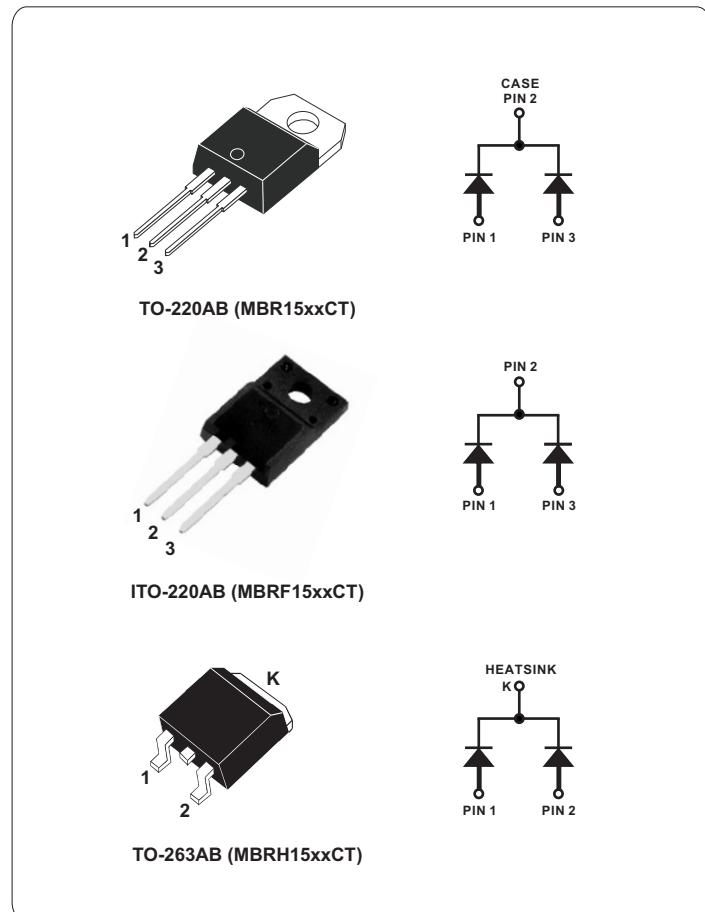
MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB
Molding compound meets UL 94 V-O
flammability rating

Terminals: Mat tin plated leads, solderable per
J-STD-002 and JESD 22-B102

Polarity: As marked

Mounting Torque: 10 in-lbs maximum



PRODUCT SUMMARY

| | |
|-----------------|------------------|
| $I_{F(AV)}$ | 7.5A x 2 |
| V_R | 45V/60V |
| V_F at I_F | 0.57V, 0.65V |
| I_{RM} max. | 15~50mA at 125°C |
| T_J max. | 150°C |
| Diode variation | Dual dice |
| E_{AS} | 7 mJ |

MAJOR RATINGS AND CHARACTERISTICS

| SYMBOL | CHARACTERISTICS | VALUE | | UNIT |
|-------------|---------------------------------|------------|-----------|------|
| | | MBR1545CT | MBR1560CT | |
| $I_{F(AV)}$ | Rectangular waveform | 7.5 x 2 | | A |
| V_{RRM} | | 45 | 60 | V |
| I_{FSM} | $t_p = 5 \mu s$ sine | 690 | | A |
| V_F | $7.5 A_{pk}, T_J = 125^\circ C$ | 0.57 | 0.65 | V |
| T_J | Range | -65 to 150 | | °C |

VOLTAGE RATINGS

| PARAMETER | SYMBOL | MBR1545CT | MBR1560CT | UNIT |
|--------------------------------------|-----------|-----------|-----------|------|
| Maximum DC reverse voltage | V_R | 45 | 60 | V |
| Maximum working peak reverse voltage | V_{RWM} | | | |

ABSOLUTE MAXIMUM RATINGS

| PARAMETER | SYMBOL | TEST CONDITIONS | VALUE | UNIT |
|--|-------------|---|-------|------|
| Maximum average forward current per device per diode | $I_{F(AV)}$ | $T_J = 105^\circ C$, rated V_R | 15 | A |
| | | | 7.5 | |
| Non-repetitive peak surge current | I_{FSM} | 5 μs sine or 3 μs rect.pulse condition and with rated V_{RRM} applied | 690 | A |
| | | Surge applied at rated load condition half wave single phase 60 Hz | 150 | |
| Non-repetitive avalanche energy | E_{AS} | $T_J = 25^\circ C$, $I_{AS} = 2.0A$, $L = 3.5mH$ | 7 | mJ |
| Repetitive avalanche current | I_{AR} | Current decaying linearly to zero in 1 μs Frequency limited by T_J maximum $V_A = 1.5 \times V_R$ typical | 2 | A |

ELECTRICAL SPECIFICATIONS

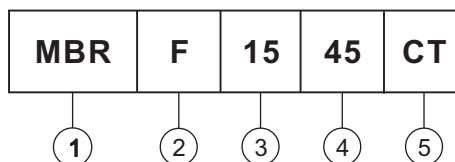
| PARAMETER | SYMBOL | TEST CONDITIONS | | VALUE | | UNIT | |
|---|----------------|--|---------------------|-------|------|------------|--|
| | | MBR1545CT | MBR1560CT | | | | |
| Maximum forward voltage drop | $V_{FM}^{(1)}$ | $I_F = 7.5A$ | $T_J = 25^\circ C$ | 0.68 | 0.75 | V | |
| | | $I_F = 15A$ | | 0.84 | 0.90 | | |
| | | $I_F = 7.5A$ | $T_J = 125^\circ C$ | 0.57 | 0.65 | | |
| | | $I_F = 15A$ | | 0.72 | 0.80 | | |
| Maximum instantaneous reverse current | $I_{RM}^{(1)}$ | $T_J = 25^\circ C$ | Rated DC voltage | 0.1 | 1 | mA | |
| | | $T_J = 125^\circ C$ | | 15 | 50 | | |
| Maximum junction capacitance | C_T | $V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz) $25^\circ C$ | | 300 | 250 | pF | |
| Typical series inductance | L_S | Measured from top of terminal to mounting plane | | 8 | | nH | |
| Maximum voltage rate of change | dV/dt | Rated V_R | | 1000 | | V/ μ s | |
| Isolation voltage (ITO-220AB only) from terminal to heatsink, t = 1 min | V_{ISO} | | | 1500 | | V | |

Note

(1) Pulse width < 300 μs , duty cycle < 2%

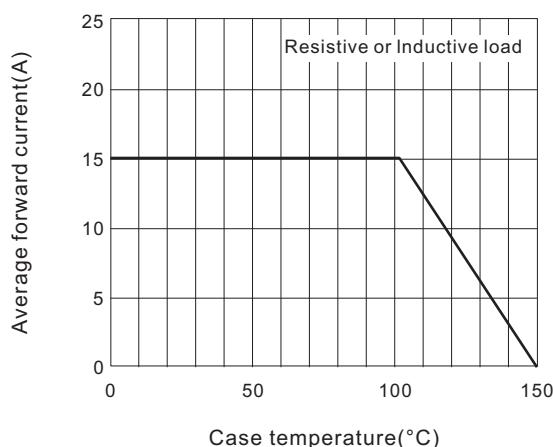
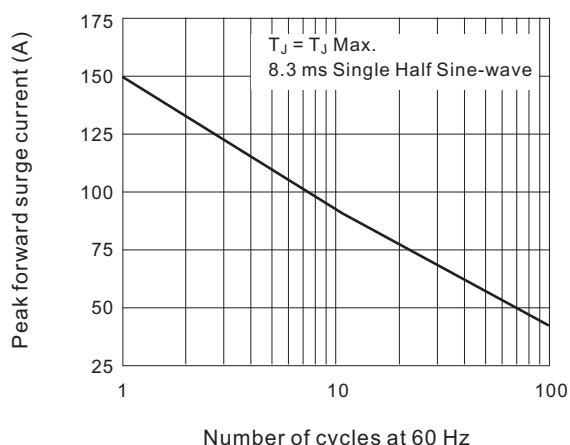
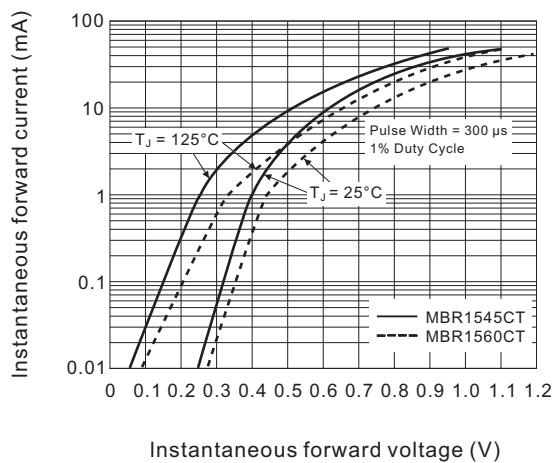
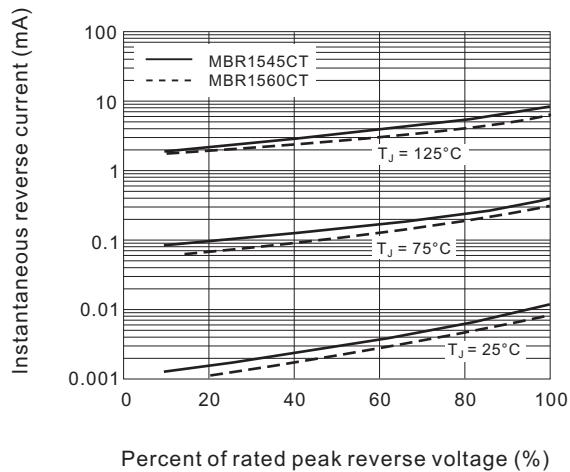
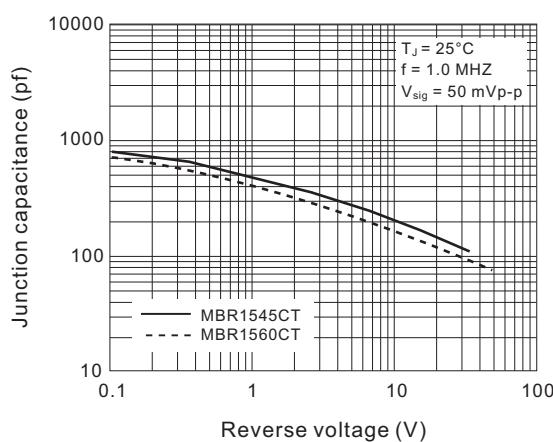
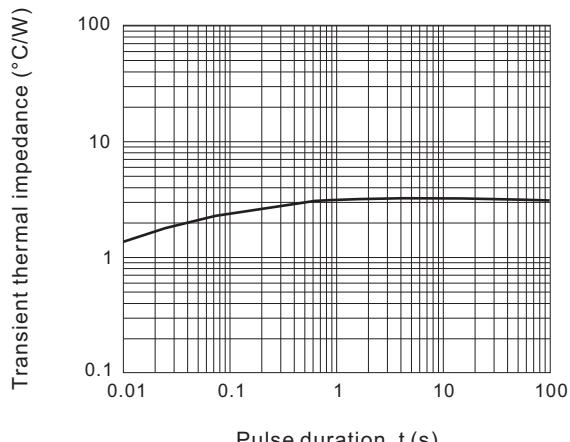
THERMAL - MECHANICAL SPECIFICATIONS

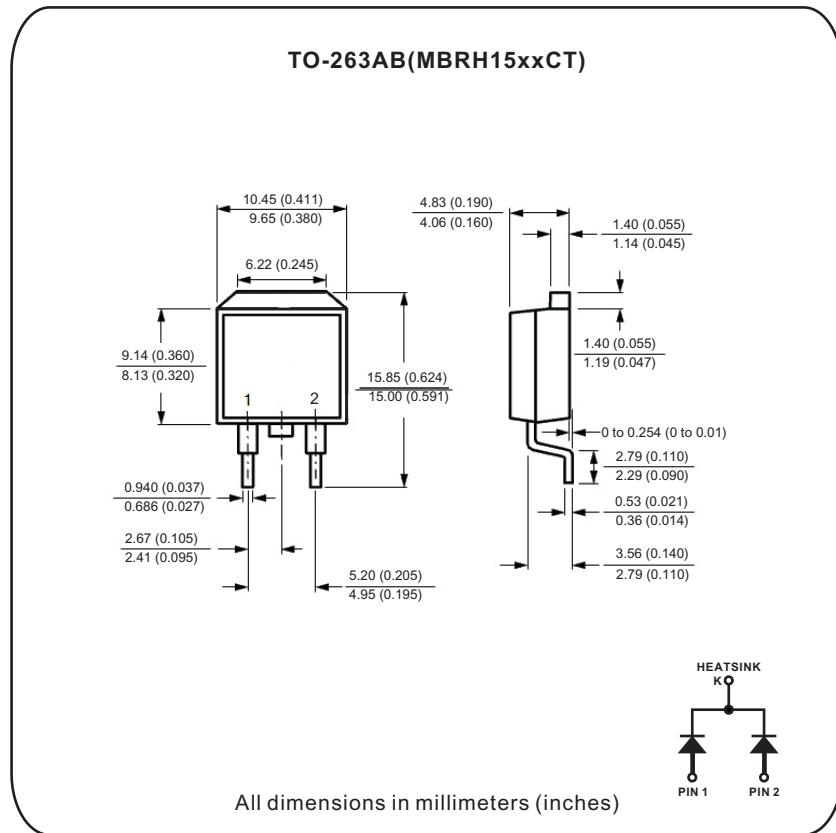
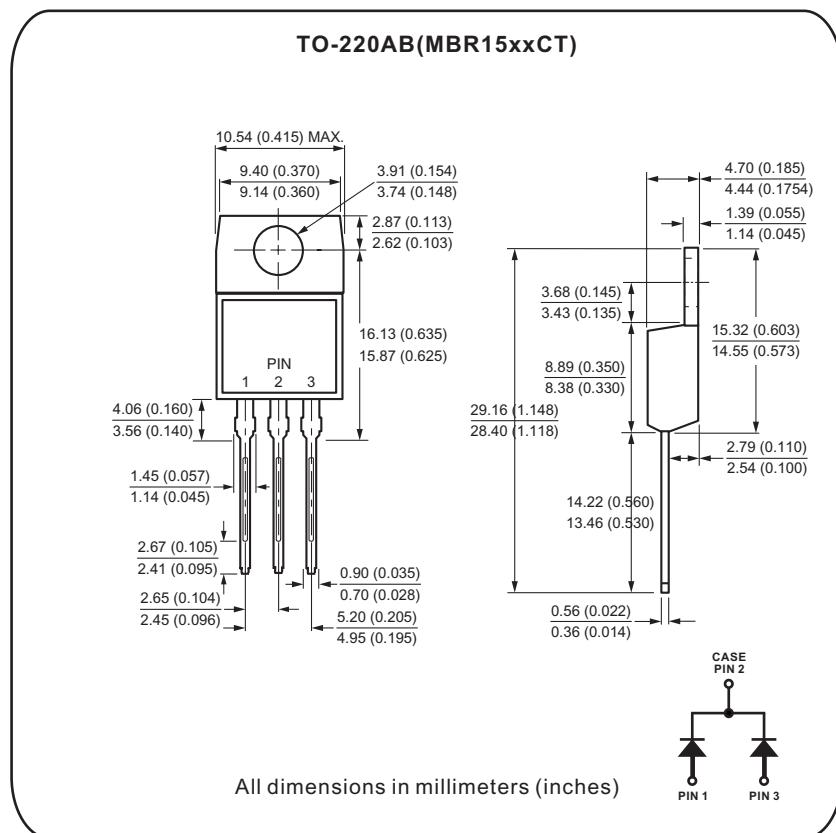
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUE | | | UNIT |
|--|------------|--------------------------------------|---------|------|------------|------------------------|
| | | | MBR | MBRF | MBRH | |
| Maximum junction temperature range | T_J | | | | -65 to 150 | °C |
| Maximum storage temperature range | T_{stg} | | | | -65 to 175 | |
| Maximum thermal resistance, junction to case | R_{thJC} | DC operation | 3 | 5 | 3 | °C/W |
| Typical thermal resistance, case to heatsink | R_{thCS} | Mounting surface, smooth and greased | 0.5 | 0.8 | 0.5 | |
| Approximate weight | | | 2 | 2 | 1.4 | g |
| | | | 0.07 | 0.07 | 0.05 | oz. |
| Mounting torque | minimum | | 6 (5) | | | kgf · cm (lbf · in) |
| | maximum | | 12 (10) | | | |

Ordering Information Table
Device code


- [1] - Schottky MBR series
- [2] - Package outline
 "none" for TO-220AB
 "F" for ITO-220AB (TO-220F)
 "H" for TO-263AB (D²PAK)
- [3] - Current rating (15 = 15A, 7.5A x 2)
- [4] - Voltage ratings, 45 = 45V, 60 = 60V
- [5] - Circuit configuration, Center tap common cathode,
 TO-220 series package

BATINGS AND CHARACTERISTICS CURVES
 $(T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig.1 Forward current derating curve

Fig.2 Maximum non-repetitive peak forward surge current per diode

Fig.3 Typical instantaneous forward characteristics per diode

Fig.4 Typical reverse characteristics per diode

Fig.5 Typical junction capacitance per diode

Fig.6 Typical transient thermal Impedance per diode




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